

SOP-8

Pin Definition:

- | | |
|-----------|----------|
| 1. Source | 8. Drain |
| 2. Source | 7. Drain |
| 3. Source | 6. Drain |
| 4. Gate | 5. Drain |

PRODUCT SUMMARY

| V_{DS} (V) | $R_{DS(on)}$ (mΩ) | I_D (A) |
|--------------|----------------------|-----------|
| 60 | 36 @ $V_{GS} = 10V$ | 4.6 |
| | 43 @ $V_{GS} = 4.5V$ | 4.2 |

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

Application

- High-Side DC/DC Conversion
- Notebook
- Server

Ordering Information

| Part No. | Package | Packing |
|---------------|---------|---------------------|
| TSM4436CS RLG | SOP-8 | 2,500pcs / 13" Reel |

Note: "G" denote for Green Product

Absolute Maximum Rating ($T_a = 25^\circ C$ unless otherwise noted)

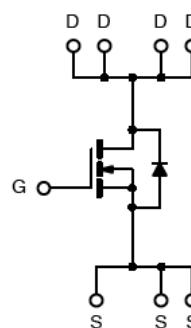
| Parameter | Symbol | Limit | Unit |
|---|----------------|-------------|------|
| Drain-Source Voltage | V_{DS} | 60 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Continuous Drain Current | I_D | 8 | A |
| Pulsed Drain Current | I_{DM} | 25 | A |
| Continuous Source Current (Diode Conduction) ^{a,b} | I_S | 2.1 | A |
| Maximum Power Dissipation | P_D | 2.5 | W |
| | | 1.6 | |
| Operating Junction Temperature | T_J | +150 | °C |
| Operating Junction and Storage Temperature Range | T_J, T_{STG} | -55 to +150 | °C |

Thermal Performance

| Parameter | Symbol | Limit | Unit |
|--|----------------|-------|------|
| Junction to Case Thermal Resistance | $R\theta_{JF}$ | 25 | °C/W |
| Junction to Ambient Thermal Resistance (PCB mounted) | $R\theta_{JA}$ | 50 | °C/W |

Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, $t \leq 10$ sec.

Block Diagram


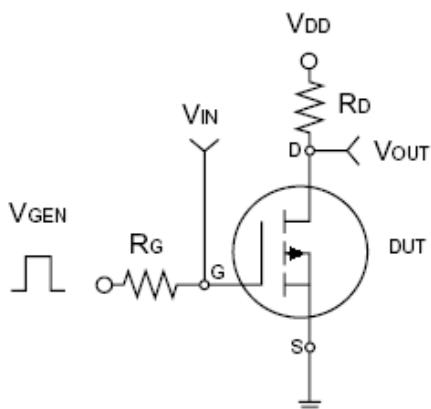
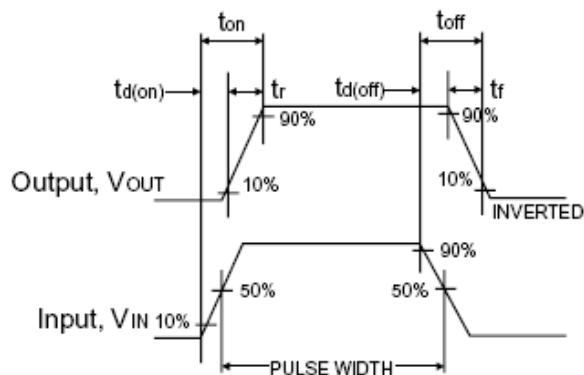
N-Channel MOSFET

Electrical Specifications

| Parameter | Conditions | Symbol | Min | Typ | Max | Unit |
|---|---|--------------|-----|------|-----------|-----------|
| Static | | | | | | |
| Drain-Source Breakdown Voltage | $V_{GS} = 0V, I_D = 250\mu A$ | BV_{DSS} | 60 | -- | -- | V |
| Gate Threshold Voltage | $V_{DS} = V_{GS}, I_D = 250\mu A$ | $V_{GS(TH)}$ | 1 | -- | 3 | V |
| Gate Body Leakage | $V_{GS} = \pm 20V, V_{DS} = 0V$ | I_{GSS} | -- | -- | ± 100 | nA |
| Zero Gate Voltage Drain Current | $V_{DS} = 60V, V_{GS} = 0V$ | I_{DSS} | -- | -- | 2 | μA |
| On-State Drain Current ^a | $V_{DS} = 5V, V_{GS} = 10V$ | $I_{D(ON)}$ | 20 | -- | -- | A |
| Drain-Source On-State Resistance ^a | $V_{GS} = 10V, I_D = 4.6A$ | $R_{DS(ON)}$ | -- | 30 | 36 | $m\Omega$ |
| | $V_{GS} = 4.5V, I_D = 4.2A$ | | -- | 35 | 43 | |
| Forward Transconductance ^a | $V_{DS} = 15V, I_D = 4.5A$ | g_{fs} | -- | 13 | -- | S |
| Diode Forward Voltage | $I_S = 2A, V_{GS} = 0V$ | V_{SD} | -- | 0.9 | 1.2 | V |
| Dynamic ^b | | | | | | |
| Total Gate Charge | $V_{DS} = 30V, I_D = 4.6A, V_{GS} = 4.5V$ | Q_g | -- | 10.5 | 16 | nC |
| Gate-Source Charge | | Q_{gs} | -- | 3.5 | -- | |
| Gate-Drain Charge | | Q_{gd} | -- | 4.2 | -- | |
| Input Capacitance | $V_{DS} = 30V, V_{GS} = 0V, f = 1.0MHz$ | C_{iss} | -- | 1100 | -- | pF |
| Output Capacitance | | C_{oss} | -- | 90 | -- | |
| Reverse Transfer Capacitance | | C_{rss} | -- | 55 | -- | |
| Switching ^c | | | | | | |
| Turn-On Delay Time | $V_{DD} = 30V, R_L = 5.4\Omega, I_D = 5.6A, V_{GEN} = 10V, R_G = 1\Omega$ | $t_{d(on)}$ | -- | 10 | 15 | nS |
| Turn-On Rise Time | | t_r | -- | 15 | 25 | |
| Turn-Off Delay Time | | $t_{d(off)}$ | -- | 25 | 40 | |
| Turn-Off Fall Time | | t_f | -- | 10 | 15 | |

Notes:

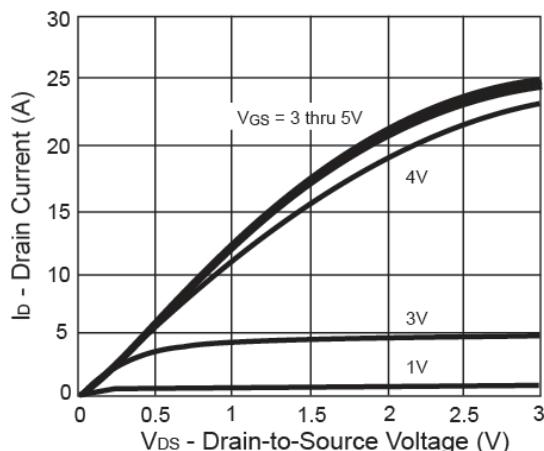
- a. pulse test: PW $\leq 300\mu S$, duty cycle $\leq 2\%$
- b. For DESIGN AID ONLY, not subject to production testing.
- c. Switching time is essentially independent of operating temperature.


Switching Test Circuit

Switching Waveforms

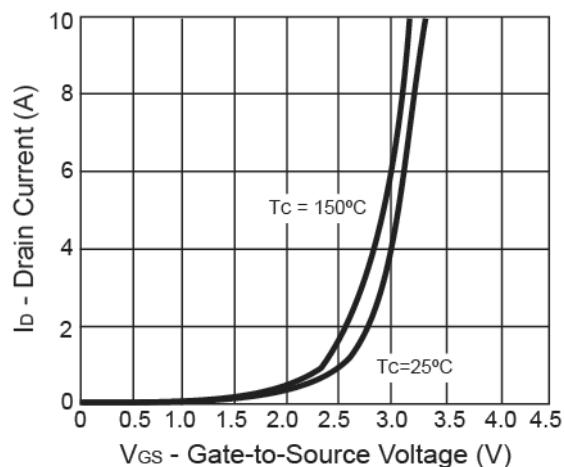


Electrical Characteristics Curve ($T_a = 25^\circ\text{C}$, unless otherwise noted)

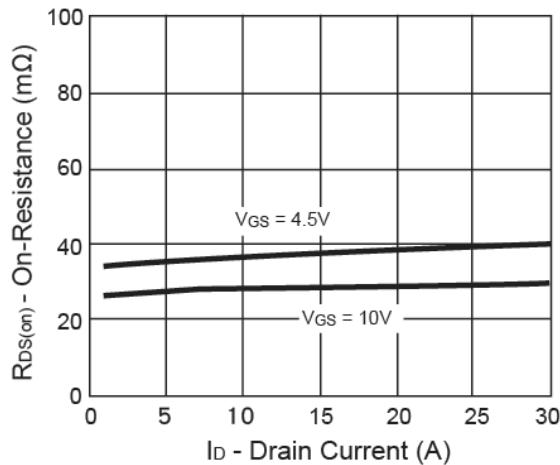
Output Characteristics



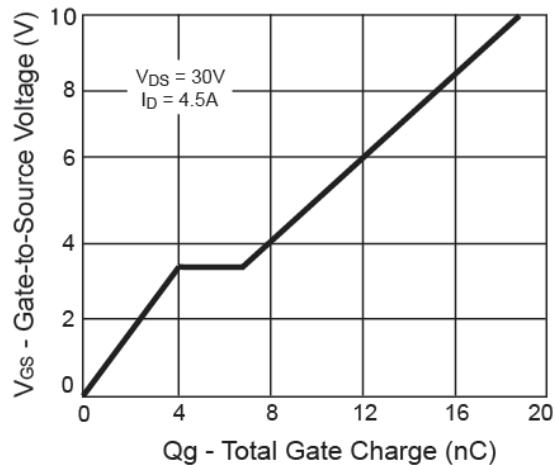
Transfer Characteristics



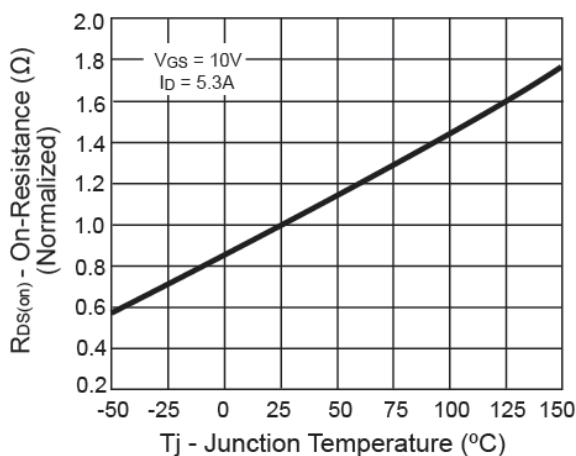
On-Resistance vs. Drain Current



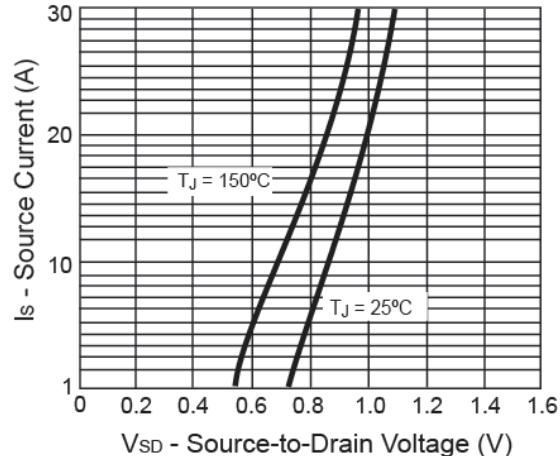
Gate Charge



On-Resistance vs. Junction Temperature



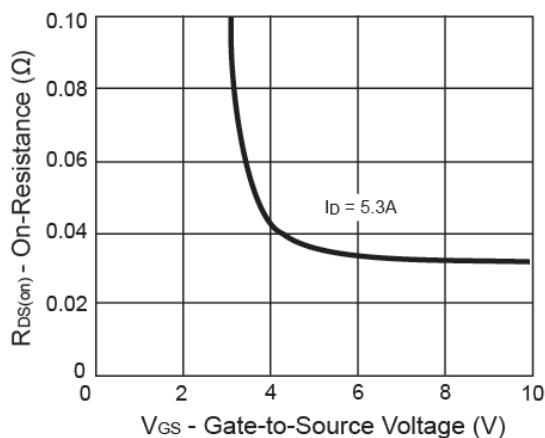
Source-Drain Diode Forward Voltage



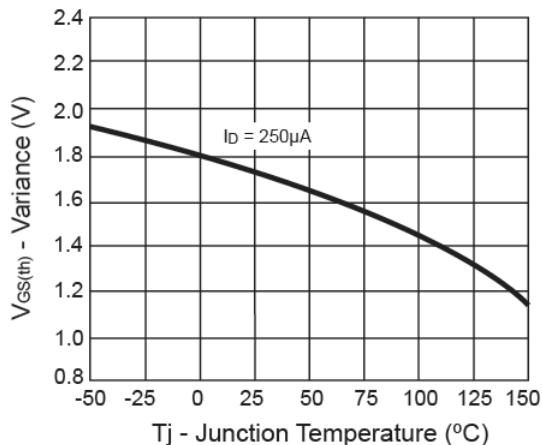


Electrical Characteristics Curve ($T_A = 25^\circ\text{C}$, unless otherwise noted)

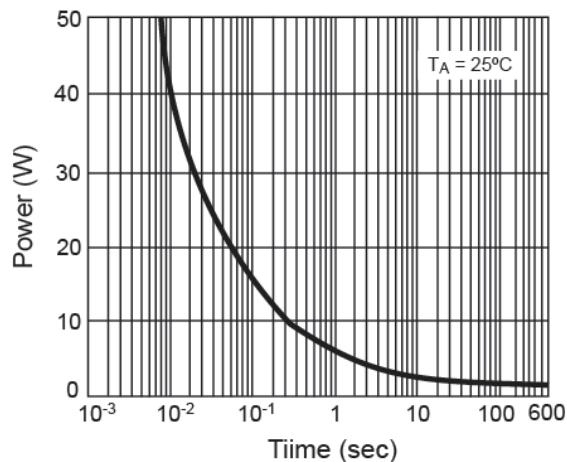
On-Resistance vs. Gate-Source Voltage



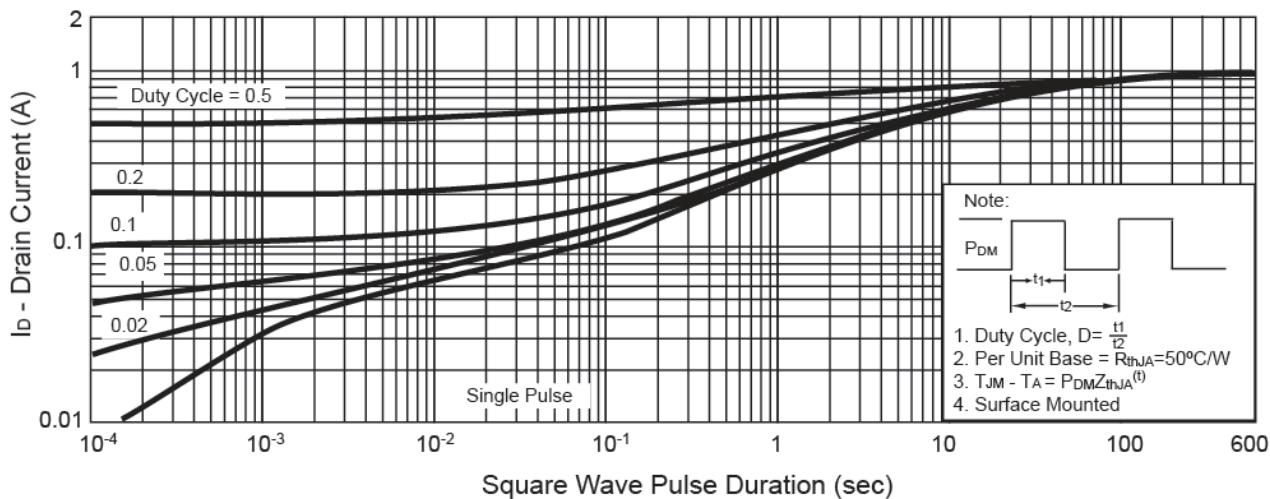
Threshold Voltage



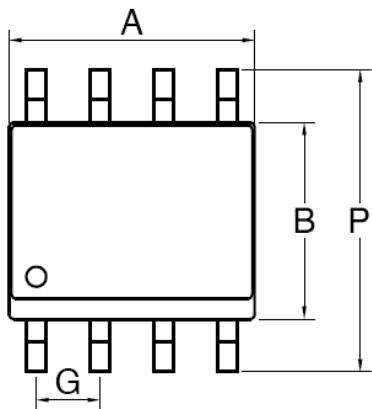
Single Pulse Power



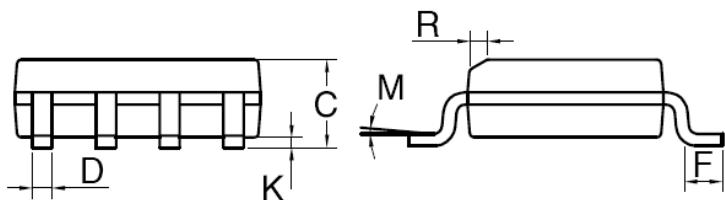
Normalized Thermal Transient Impedance, Junction-to-Ambient



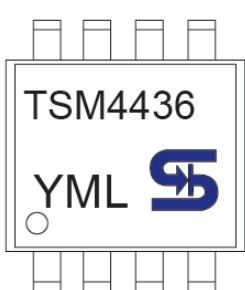
SOP-8 Mechanical Drawing



| SOP-8 DIMENSION | | | | |
|-----------------|-------------|------|---------|-------|
| DIM | MILLIMETERS | | INCHES | |
| | MIN | MAX | MIN | MAX. |
| A | 4.80 | 5.00 | 0.189 | 0.196 |
| B | 3.80 | 4.00 | 0.150 | 0.157 |
| C | 1.35 | 1.75 | 0.054 | 0.068 |
| D | 0.35 | 0.49 | 0.014 | 0.019 |
| F | 0.40 | 1.25 | 0.016 | 0.049 |
| G | 1.27BSC | | 0.05BSC | |
| K | 0.10 | 0.25 | 0.004 | 0.009 |
| M | 0° | 7° | 0° | 7° |
| P | 5.80 | 6.20 | 0.229 | 0.244 |
| R | 0.25 | 0.50 | 0.010 | 0.019 |



Marking Diagram



Y = Year Code

M = Month Code for Halogen Free Product

O =Jan P =Feb Q =Mar R =Apr

S =May T =Jun U =Jul V =Aug

W =Sep X =Oct Y =Nov Z =Dec

L = Lot Code



TSM4436
60V N-Channel MOSFET

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